

E U R O P E A N P A T E N T O F F I C E

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MC : L04-A L04-C11C L04-C16
U11-C05F3A U11-C05F6 U12-A01A2 U12-A01B2 V08-A01B V08-A04A

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PR : JP930085492 930319

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IC : H01L33/00 ;H01S3/18

TI : Electrode formation method for gallium nitride compound semiconductor
- involving adhesive of metallic or alloy layer to semiconductor
followed by annealing

AB : J06275868 The process first involves adhering a layer made up of
either chromium or nickel, or an alloy of both, onto a gallium
nitride- type compound semiconductor. If this is an n-type gallium
nitride semiconductor, it should have a carrier density beyond 1×10
power 17 electrons/cc, and if it is a p-type gallium nitride compound
semiconductor, then its whole carrier density must be greater than 1×10
power 15 holes/cc. Following the adherence of the metallic or alloy
layer, the semiconductor is subjected to annealing.
ADVANTAGE - Raises emission output of light emitting element that use
the pn junction of gallium nitride type compound semiconductor.
Improves efficiency of operation.
(Dwg.1/3)